CRMTGH2222A

N-Channel 220V, 19mΩ Typ. Power MOSFET

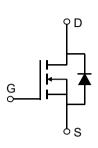
Description

Features

• 220V, 85A

 $R_{DS(ON)}$ Typ = 19m Ω @ V_{GS} = 10V Advanced Split Gate Trench Technology

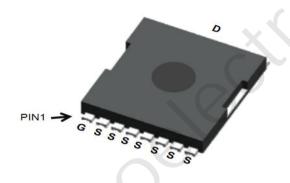
- Excellent R_{DS(ON)} and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!

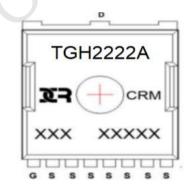




Application

- Load Switch
- PWM Application
- Power Management





Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMTGH2222A	CRMTGH2222A	TOLL	TAPING	13"	2000	10000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		220	V
V _{GS}	Gate-to-Source Voltage		±20	V
	Continuous Drain Current $\frac{T_{C} = 25^{\circ}C}{T_{C} = 100^{\circ}C}$	T _C = 25°C	85	Α
I _D		T _C = 100°C	51	А
I _{DM}	Pulsed Drain Current (1)		340	А
E _{AS}	Single Pulsed Avalanche Energy (2)		72	mJ
P_{D}	Power Dissipation	T _C = 25°C	357	W
$R_{ heta JC}$	Thermal Resistance, Junction to Case		0.35	°C/W
T_{J} , T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Parameter	Conditions	Min.	Тур.	Max.	Unit
			ı yp.	Wax.	Ullil
cteristics					
Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	220	-	-	V
Zero Gate Voltage Drain Current	$V_{DS} = 220V, V_{GS} = 0V$	-	-	1.0	μΑ
Gate-Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±100	nA
cteristics				6	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5	3.5	4.5	V
Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 30A	-	19	24.7	mΩ
Characteristics					
Input Capacitance		-	5282	-	pF
Output Capacitance	$V_{GS} = 0V, V_{DS} = 100V,$	-	334	-	pF
Reverse Transfer Capacitance	I - IIVIIIZ	X -	11	-	pF
Total Gate Charge		-	72	-	nC
Gate Source Charge	**) .	28	-	nC
Gate Drain("Miller") Charge	v _{DS} - 100v, I _D - 30A	-	18	-	nC
Characteristics					
Turn-On DelayTime		-	16	-	ns
Turn-On Rise Time	$V_{GS} = 10V, V_{DD} = 100V$	-	15	-	ns
Turn-Off DelayTime	I_{D} = 30A, R_{GEN} = 4.7 Ω	-	46	-	ns
Turn-Off Fall Time		-	9	-	ns
rce Diode Characteristics and M	lax Ratings				
Maximum Continuous Drain to Source Diode Forward Current		-	-	85	Α
Maximum Pulsed Drain to Source Diode Forward Current		-	-	340	Α
Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 30A	-	-	1.2	V
Body Diode Reverse Recovery Time		-	177	-	ns
Body Diode Reverse Recovery Charge	$I_F = 30A$, di/dt = 100A/us	_	500	-	nC
	Zero Gate Voltage Drain Current Gate-Body Leakage Current Eteristics Gate Threshold Voltage Static Drain-Source ON-Resistance ⁽³⁾ Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Fotal Gate Charge Gate Source Charge Gate Drain("Miller") Charge Characteristics Furn-On DelayTime Furn-Off DelayTime Furn-Off Fall Time Tree Diode Characteristics and November 1 and	Zero Gate Voltage Drain Current VDS = 220V, VGS = 0V Gate-Body Leakage Current VDS = 0V, VGS = $\pm 20V$ Steristics Gate Threshold Voltage VDS = VGS, ID = $\pm 250\mu$ A Static Drain-Source ON-Resistance Static Drain-Source ON-Resistance Output Capacitance Output Capacitance Output Capacitance Fotal Gate Charge Gate Source Charge Gate Drain("Miller") Charge Characteristics Furn-On DelayTime Furn-On Rise Time Furn-Off DelayTime Furn-Off Fall Time Furn-Off Fall Time Force Diode Characteristics and Max Ratings Maximum Continuous Drain to Source Diode Forward Current Maximum Pulsed Drain to Source Diode Forward Current Orain to Source Diode Reverse Recovery Time Fig. 30A, di/dt = 100A/us	Zero Gate Voltage Drain Current $V_{DS} = 220V, V_{GS} = 0V$ - Gate-Body Leakage Current $V_{DS} = 0V, V_{GS} = 220V$ - Steteristics Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250\mu A$ 2.5 Static Drain-Source ON-Resistance ⁽³⁾ $V_{GS} = 10V, I_D = 30A$ - Characteristics Input Capacitance $V_{GS} = 0V, V_{DS} = 100V, I_D = 30A$ - Characteristics Input Capacitance $V_{GS} = 0V, V_{DS} = 100V, I_D = 30A$ - Characteristics For tall Gate Charge $V_{GS} = 0$ to $10V$ - Gate Source Charge $V_{GS} = 0$ to $10V$ - Gate Drain("Miller") Charge $V_{GS} = 100V, I_D = 30A$ - Characteristics Furn-On DelayTime $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off DelayTime $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Fall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Fall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DD} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DS} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DS} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DS} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{DS} = 100V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{GS} = 10V, V_{GS} = 10V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{GS} = 10V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{GS} = 10V$ - Furn-Off Pall Time $V_{GS} = 10V, V_{GS} = 10V$ - Furn-Off Pall Time $V_{GS} = 10V$ -	Zero Gate Voltage Drain Current $V_{DS} = 220V, V_{GS} = 0V$ Gate-Body Leakage Current $V_{DS} = 220V, V_{GS} = \pm 20V$	Zero Gate Voltage Drain Current $V_{DS} = 220V$, $V_{GS} = 0V$ - 1.0 Gate-Body Leakage Current $V_{DS} = 0V$, $V_{GS} = \pm 20V$ - ± 100 Exteristics Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250\mu A$ 2.5 3.5 4.5 Static Drain-Source ON-Resistance ⁽³⁾ $V_{GS} = 10V$, $I_D = 30A$ - 19 24.7 Characteristics Input Capacitance $V_{GS} = 0V$, $V_{DS} = 100V$, $I_D = 30A$ - 334 - 10 Static Drain-Source Capacitance $V_{GS} = 0V$, $V_{DS} = 100V$, $I_D = 30A$ - 11 - 72 - 72 Gate Source Charge $V_{GS} = 0$ to $10V$ $V_{DS} = 100V$, $I_D = 30A$ - 18 - 72 Characteristics Furn-On DelayTime $V_{GS} = 100V$, $V_{DS} = 100V$ - 15 - 74 Grunn-On Rise Time $V_{GS} = 10V$, $V_{DD} = 100V$ - 15 - 75 Gurn-Off DelayTime $V_{GS} = 10V$, $V_{DD} = 100V$ - 15 - 75 Gurn-Off Fall Time $V_{GS} = 10V$, $V_{DD} = 100V$ - 15 - 75 Gurn-Off Fall Time $V_{GS} = 10V$, $V_{DD} = 100V$ - 15 - 75 Gurn-Off Fall Time $V_{GS} = 10V$, $V_{DS} = 100V$ - 15 - 16 Gurn-Off Fall Time $I_D = 30A$, $I_D = 30A$ - 12 Grain to Source Diode Forward Current $I_D = 30A$, $I_D = 30A$ - 12 Grain to Source Diode Forward Voltage $I_D = 30A$, $I_D = 30A$ - 177 - 177 - 177 - 177 Gody Diode Reverse Recovery Time $I_D = 30A$, $I_D = 30A$ - 177 - 177 - 177 Gody Diode Reverse Recovery Time $I_D = 30A$, $I_D = 30A$ - 177 - 177 - 177 Gody Diode Reverse Recovery Time $I_D = 30A$, $I_D = 30A$ - 177 - 177 Gody Diode Reverse Recovery Time $I_D = 30A$, $I_D = 30A$ - 177 - 177 Gody Diode Reverse Recovery Time $I_D = 30A$, $I_D = 30A$

Notes:

^{1.} Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

^{2.} E_{AS} condition: Starting T_J =25°C, V_{DD} =30V, V_G =10V, R_G =25ohm, L=0.5mH, I_{AS} =17A

^{3.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%.

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Test Circuit

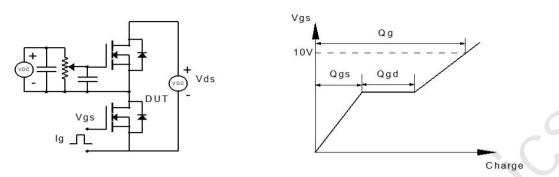


Figure 1: Gate Charge Test Circuit & Waveform

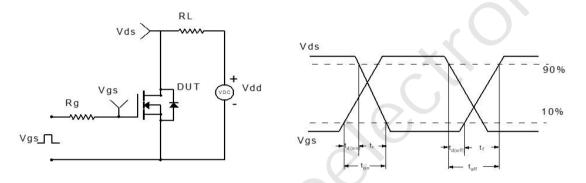


Figure 2: Resistive Switching Test Circuit & Waveform

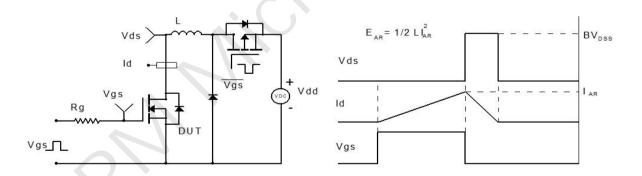


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

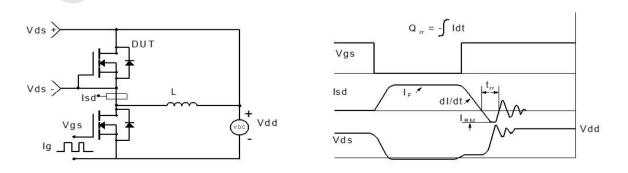
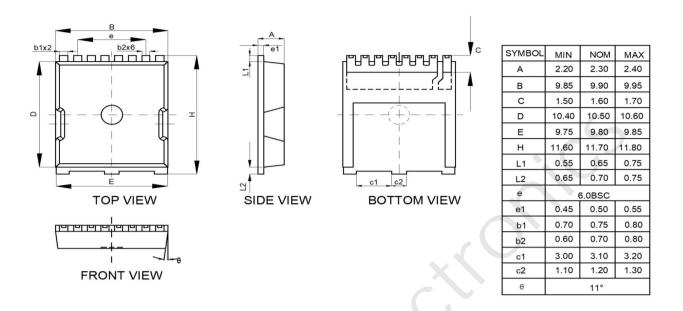


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(TOLL)



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